

AMENDMENTS TO THE CLAIMS

Claims 1-25 (Canceled)

Claim 26 (Previously Presented): A chemical mechanical polishing process comprising:

polishing of an interlayer insulating film with an elastic modulus of no greater than 20 GPa as measured by the nanoindentation method, using an aqueous dispersion which comprises a scratch inhibitor and an abrasive comprising organic/inorganic composite particle,

wherein said scratch inhibitor is at least one compound selected from the group consisting of (1) biphenol, (2) bipyridyl, (3) 2-vinylpyridine and 4-vinylpyridine, (4) salicylaldehyde, (5) o-phenylenediamine and m-phenylenediamine, (6) catechol, (7) o-aminophenol, (8) thiourea, (9) an N-alkyl group-containing (meth)acrylamide, (10) an N-aminoalkyl group-containing (meth)acrylamide, (11) a heterocyclic compound with a heteropentacycle and with no aromatic ring forming the skeleton, (12) a heterocyclic compound with a heteropentacycle and with an aromatic ring forming the skeleton, (13) phthalazine, (14) a compound with a heterohexacycle bearing three nitrogen atoms and a derivative of any of compounds (1) through (14), and (15) a surfactant and,

wherein said abrasive comprising organic/inorganic composite particle has an organic particle and an inorganic particle with zeta potentials of opposite signs bonded by electrostatic force.

Claim 27 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said scratch inhibitor is a non-ionic surfactant which is one selected from the group consisting of polyoxyethylene alkyl ether, polyoxyethylene ether of glycerin ester, polyethylene glycol fatty acid ester, glycerin ester and sorbitan ester.

Claim 28 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said scratch inhibitor is 7-hydroxy-5-methyl-1,3,4-triazaindolizine.

Claim 29 (Previously Presented): The chemical mechanical polishing process according to claim 26, wherein said scratch inhibitor comprises a combination of a compound selected from the group consisting of 7 hydroxy-5-methyl-1,3,4-triazaindolizine and 5-amino-1H-tetrazole, and a non-ionic surfactant.

Claim 30 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said aqueous dispersion further comprises an oxidizing agent.

Claim 31 (Previously Presented): The chemical mechanical polishing process according to Claim 30, wherein said oxidizing agent is hydrogen peroxide.

Claim 32 (Previously Presented): The chemical mechanical polishing process according to Claim 30, wherein said aqueous dispersion further comprises an organic acid.

Claim 33 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said scratch inhibitor is a surfactant which is present in an amount of from 0.0001 to 0.1 wt%, and another scratch inhibitor, other than the surfactant, present in an amount of from 0.001 to 5 wt%, based on the weight of the aqueous dispersion.

Claim 34 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said abrasive is present in an amount of from 0.1 to 20 parts by weight, based on 100 parts of the aqueous dispersion.

Claim 35 (Previously Presented): The chemical mechanical polishing process according to Claim 26, wherein said aqueous dispersion has a pH of from 2 to 12.

Claim 36 (Previously Presented): The chemical mechanical polishing process according to Claim 30, wherein said oxidizing agent is present in an amount of from 0.01 to 3 parts by weight, based on 100 parts of the aqueous dispersion.